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ATTORNEY'S DOCKET NUMBER

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U.S. APPLICATION NO. (IF KNOWN, SEE 37 CFR

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INTERNATIONAL APPLICATION NO.  
**PCT/JP98/04983**INTERNATIONAL FILING DATE  
**05 NOVEMBER 1998**

PRIORITY DATE CLAIMED

**05 NOVEMBER 1997 EARLIEST**

## TITLE OF INVENTION

**WIRING STRUCTURE AND ELECTRODE OF SEMICONDUCTOR DEVICE AND METHOD OF  
MANUFACTURING THE SAME**

## APPLICANT(S) FOR DO/BO/US

Kimihiro MATSUSE, et al

Applicant herewith submits to the United States Designated/Elected Office (DO/EO/US) the following items and other information:

- This is a **FIRST** submission of items concerning a filing under 35 U.S.C. 371.
- This is a **SECOND** or **SUBSEQUENT** submission of items concerning a filing under 35 U.S.C. 371.
- This is an express request to begin national examination procedures (35 U.S.C. 371(f)) at any time rather than delay examination until the expiration of the applicable time limit set in 35 U.S.C. 371(b) and PCT Articles 22 and 39(1).
- A proper Demand for International Preliminary Examination was made by the 19th month from the earliest claimed priority date.
- A copy of the International Application as filed (35 U.S.C. 371 (c) (2))
  - is transmitted herewith (required only if not transmitted by the International Bureau).
  - has been transmitted by the International Bureau.
  - is not required, as the application was filed in the United States Receiving Office (RO/US).
- A translation of the International Application into English (35 U.S.C. 371(c)(2)).
- A copy of the International Search Report (PCT/ISA/210).
- Amendments to the claims of the International Application under PCT Article 19 (35 U.S.C. 371 (c)(3))
  - are transmitted herewith (required only if not transmitted by the International Bureau).
  - have been transmitted by the International Bureau.
  - have not been made; however, the time limit for making such amendments has NOT expired.
  - have not been made and will not be made.
- A translation of the amendments to the claims under PCT Article 19 (35 U.S.C. 371(c)(3)).
- An oath or declaration of the inventor(s) (35 U.S.C. 371 (c)(4)).
- A copy of the International Preliminary Examination Report (PCT/IPEA/409).
- A translation of the annexes to the International Preliminary Examination Report under PCT Article 36 (35 U.S.C. 371 (c)(5)).

## Items 13 to 18 below concern document(s) or information included:

- An Information Disclosure Statement under 37 CFR 1.97 and 1.98.
- An assignment document for recording. A separate cover sheet in compliance with 37 CFR 3.28 and 3.31 is included.
- A **FIRST** preliminary amendment.
- A **SECOND** or **SUBSEQUENT** preliminary amendment.
- A substitute specification.
- A change of power of attorney and/or address letter.
- Certificate of Mailing by Express Mail
- Other items or information:

Notice of Priority

Drawings (4 sheets)

Two Articles 34, Amended Sheets 31-36

Request For Consideration of Documents Cited in International Search Report

U.S. APPLICATION NO. (IF KNOWN, SEE AT CTR)	INTERNATIONAL APPLICATION NO.	ATTORNEY'S DOCKET NUMBER
<b>09/530588</b>	PCT/JP98/04983	2312-0866-2PCT

20. The following fees are submitted.:

**BASIC NATIONAL FEE (37 CFR 1.492 (a) (1) - (5)) :**

<input checked="" type="checkbox"/> Search Report has been prepared by the EPO or JPO .....	\$840.00
<input type="checkbox"/> International preliminary examination fee paid to USPTO (37 CFR 1.482) .....	\$670.00
<input type="checkbox"/> No international preliminary examination fee paid to USPTO (37 CFR 1.482) but international search fee paid to USPTO (37 CFR 1.445(a)(2)) .....	\$760.00
<input type="checkbox"/> Neither international preliminary examination fee (37 CFR 1.482) nor international search fee (37 CFR 1.445(a)(2)) paid to USPTO .....	\$970.00
<input type="checkbox"/> International preliminary examination fee paid to USPTO (37 CFR 1.482) and all claims satisfied provisions of PCT Article 33(2)-(4) .....	\$96.00

**CALCULATIONS PTO USE ONLY****ENTER APPROPRIATE BASIC FEE AMOUNT =**

\$840.00

Surcharge of \$130.00 for furnishing the oath or declaration later than months from the earliest claimed priority date (37 CFR 1.492 (e)).  20  30

\$0.00

CLAIMS	NUMBER FILED	NUMBER EXTRA	RATE
Total claims	18 - 20 =	0	x \$18.00
Independent claims	4 - 3 =	1	x \$78.00
Multiple Dependent Claims (check if applicable). <input checked="" type="checkbox"/>			
<b>TOTAL OF ABOVE CALCULATIONS =</b>			
Reduction of 1/2 for filing by small entity, if applicable. Verified Small Entity Statement must also be filed (Note 37 CFR 1.9, 1.27, 1.28) (check if applicable). <input type="checkbox"/>			
<b>SUBTOTAL =</b>			
Processing fee of \$130.00 for furnishing the English translation later than months from the earliest claimed priority date (37 CFR 1.492 (f)). <input type="checkbox"/> 20 <input type="checkbox"/> 30 +			
<b>TOTAL NATIONAL FEE =</b>			
Fee for recording the enclosed assignment (37 CFR 1.21(h)). The assignment must be accompanied by an appropriate cover sheet (37 CFR 3.28, 3.31) (check if applicable). <input type="checkbox"/>			
<b>TOTAL FEES ENCLOSED =</b>			
<input checked="" type="checkbox"/> Amount to be: <input type="checkbox"/> refunded \$ <input type="checkbox"/> charged \$ 			

- A check in the amount of **\$1,178.00** to cover the above fees is enclosed.
- Please charge my Deposit Account No. **15-0030** in the amount of **\$** to cover the above fees. A duplicate copy of this sheet is enclosed.
- The Commissioner is hereby authorized to charge any fees which may be required, or credit any overpayment to Deposit Account No. **15-0030** A duplicate copy of this sheet is enclosed.

NOTE: Where an appropriate time limit under 37 CFR 1.494 or 1.495 has not been met, a petition to revive (37 CFR 1.137(a) or (b)) must be filed and granted to restore the application to pending status.

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## D E S C R I P T I O N

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WIRING STRUCTURE AND ELECTRODE OF  
SEMICONDUCTOR DEVICE AND METHOD OF  
MANUFACTURING THE SAME

## Technical Field

The present invention relates to a wiring structure and an electrode of a semiconductor device, 10 and a method of manufacturing the same.

## Background Art

Generally, to manufacture a semiconductor integrated device such as a semiconductor integrated circuit, film-formation, oxidative diffusion, etching 15 and the like are repeatedly applied onto a semiconductor wafer to form numeral transistors, capacitors, and resistances, and thereafter these elements are connected with a wiring pattern. Furthermore, since the development of a high-performance integrated 20 circuit and a multi-functional integrated circuit has been demanded, a further reduction of wiring width and higher integration of the elements are demanded. Moreover, a multi-layered structure has come to be employed in which circuits themselves are stacked one 25 upon the other with an insulating layer interposed between them.

Since a sectional area of the wiring and a connecting portion is reduced under these circumstances, there is a tendency of increasing

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resistance. It follows that, as a wiring material,  
copper tends to be used in place of aluminium used  
generally at present. This is because copper is highly  
resistant to electromigration and its resistivity is  
5 relatively low even though form-formation is not so  
easy as aluminum.

Usually, as a gate electrode used in a transistor  
element, a doped polysilicon layer is used alone or  
a double layered structure electrode is used which is  
10 formed by stacking a molybdenum silicide layer or  
a tungsten silicide layer on the doped polysilicon  
layer. However, to further reduce the resistivity,  
an attempt has been made to replace upper silicide  
layer of the double-layered gate electrode with  
15 a single metal layer, for example, a tungsten layer.

Incidentally, copper and tungsten themselves are  
highly active metals, so that they are likely to react  
with other elements. For example, metal copper has  
a large diffusion coefficient, so that it diffuses and  
20 segregates into Si, SiO<sub>2</sub> or the like, causing defects.  
As a result, not only resistance value increases but  
also exfoliation occurs.

When a metal tungsten film is used as one of the  
layers of the gate electrode of the double layered  
25 structure, the silicon atoms of the lower doped  
polysilicon layer and tungsten of the upper metal  
tungsten layer are mutually diffused and react with

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each other to produce tungsten silicide having a large resistivity.

To prevent the reaction between the metal copper and the metal tungsten, it is possible to use a barrier metal such as TiN (titanium nitride) as conventionally used. However, the TiN layer is not a preferable barrier metal because affinity, in other words, adhesiveness, with the metal copper film and the metal tungsten film, is not satisfactory.

Recently, the semiconductor integrated circuit has been desired to be formed in more integrated and more multi-layered structure and operated at a higher speed. To satisfy these demands, it is required to reduce a resistivity of a gate electrode, for example, by reducing the thickness of individual layers and to increase an aspect ratio (a high aspect ratio) during etching processing.

However, if the thickness of a tungsten film constituting the gate electrode is reduced, the tungsten film degrades in adhesiveness to an underlying layer, for example, the polysilicon layer, and in heat resistance. It is also possible herein that a conventionally known TiN film is interposed between both layers as a barrier metal. However, in this case, the adhesiveness between the TiN film and the polysilicon film at the interface degrades, causing exfoliation.

## Disclosure of Invention

An object of the present invention is to provide  
a wiring structure and an electrode of a semiconductor  
device including a barrier metal which is effective for  
5      a metal copper film and a metal tungsten film, and to  
provide a method of manufacturing the same. Another  
object of the present invention is to provide a gate  
electrode excellent in characteristics even if the  
thickness is reduced and a method of manufacturing  
10     the same.

To attain the aforementioned object, the wiring  
structure of the semiconductor device according to the  
present invention comprises

15     a first conducting layer electrically connected to  
a semiconductor element or a wiring element formed on  
a semiconductor substrate;

a barrier metal formed on the first conducting  
layer; and

20     a second conducting layer formed on the barrier  
metal and electrically connected to the first  
conducting layer via the barrier metal;

in which the barrier metal is formed of  $WN_x$   
(tungsten nitride) or  $WSixNy$  (tungsten silicide  
nitride).

25     Furthermore, the present invention is directed  
to an electrode of a circuit element formed on  
a semiconductor substrate, comprising a polysilicon

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layer, a barrier metal formed on the polysilicon layer and a metal layer formed on the barrier metal, in which the barrier metal is formed of  $WN_x$  (tungsten nitride) or  $WSixNy$  (tungsten silicide nitride).

5 The present invention is directed to a method of manufacturing a wiring structure of a semiconductor device.

forming a first conducting layer by depositing a metal film on an insulating film of the semiconductor device;

forming an interlayer insulating film over an entire surface of the semiconductor substrate so as to cover the first conducting layer from the above;

15 forming a connecting hole at a predetermined position of the interlayer insulating film so as to pass the interlayer insulating film and reach the first conducting layer;

20 forming a barrier metal of  $WN_x$  (tungsten nitride) or  $WSixNy$  (tungsten silicide nitride) from an inner surface of the connecting hole to a surface of the first conducting layer exposed in a bottom portion of the connecting hole; and

depositing a metal film on the barrier metal and simultaneously fill the connecting hole with the metal film, thereby forming a second conducting layer electrically connected with the first conducting layer via the barrier metal.

Furthermore, the present invention is directed to  
a method of forming a gate electrode of a transistor  
formed on a semiconductor substrate, comprising  
forming a polysilicon layer on a gate oxide film  
5 formed between a source and a drain of the transistor;  
forming a barrier metal of  $WN_x$  (tungsten nitride)  
or  $WSixNy$  (tungsten silicide nitride), thereby forming  
a metal layer on a barrier metal.

Brief Description of Drawings

10 FIG. 1 is an enlarged sectional view showing  
a barrier metal applied to Cu dual damashine wiring.

FIG. 2 is an enlarged sectional view showing  
a barrier metal applied to a contact hole.

15 FIG. 3 is an enlarged sectional view showing  
a barrier metal applied to a gate electrode.

FIG. 4 is an enlarged sectional view showing  
a barrier metal applied to a capacitor electrode.

FIG. 5 is a schematic structural view showing  
a processing apparatus for forming a barrier metal.

20 FIGS. 6A to 6F are views for use in explaining  
a Cu dual damashine process.

FIG. 7 is an enlarged view showing a part of  
the electrode shown in FIG. 3.

25 FIG. 8 is an enlarged sectional view of a gate  
electrode using  $Ta_2O_5$  as a gate oxide film.

FIG. 9 is data for comparing the gate electrode  
according to the present invention to a conventional

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gate electrode.

Best Mode for Carrying Out the Invention

Now, embodiments of the present invention will be explained with reference to the drawings.

5 FIG. 1 is an enlarged sectional view showing a barrier metal applied to Cu dual damashine wiring. FIG. 2 is an enlarged sectional view showing a barrier metal applied to a contact hole. FIG. 3 is an enlarged 10 sectional view showing a barrier metal applied to a gate electrode. FIG. 4 is an enlarged sectional view showing a barrier metal applied to a capacitor electrode.

The dual damashine process for forming Cu dual damashine wiring as shown in FIG. 1 is used 15 for the multi-layered structure of wiring to attain a high-performance and multi-functional device in a semiconductor integrated device, namely, a semiconductor integrated circuit. More specifically, in the case where wiring is formed in the multi-layered 20 structure, an upper layer wiring element is connected to a lower layer wiring element. At this time, this process makes it possible to form wiring and via-plug simultaneously, with the result that the number of steps, and the cost for wiring can be successfully 25 reduced, and the aspect ratio can be successfully high.

In FIG. 1, reference numeral 2 is, for example, a substrate such as a semiconductor wafer, a reference

numeral 4 is a lower-layer wiring element (conducting layer) formed on a surface of the substrate 2. The lower-layer wiring element 4 is insulated by, for example, SiO<sub>2</sub> insulating film 6 formed therearound.

5 The lower-layer wiring 4 is formed of, for example, a metal copper thin film. Reference numeral 8 is an interlayer insulating film made of SiO<sub>2</sub> formed by SOG (Spin On Glass) so as to cover the SiO<sub>2</sub> insulating film 6 and the lower-layer wiring element 4. The interlayer insulating film 8 is formed by coating in accordance 0 with SOG as mentioned above, so that a relatively large number of oxygen molecules are contained.

Reference numeral 10 is a via-hole formed in  
the interlayer insulating film 8 so as to expose  
15 a part of the lower-layer wiring element 4. Reference numeral 12 is a wiring groove formed in the surface of the interlayer insulating film 8. Reference numeral 14 is a thin barrier metal of  $WN_x$  (tungsten nitride;  $x = 0.5-1$ ) or  $WSixNy$  (tungsten silicide nitride;  $x = 0.01-0.2$ ,  $y = 0.02-0.2$ ) according to the present invention. The barrier metal is formed on an inner wall surface of the via-hole 10 and on an inner wall surface of the wiring groove 12. Reference numeral 16 is an upper layer wiring element (conducting layer) formed of, for example, a metal copper. When the wiring is formed, the via-hole 10 is filled with the metal copper, with the result that a via-hole plug 16A

is simultaneously formed.

In this case, the width L1 of the wiring element 16 is 1  $\mu\text{m}$  or less, for example, about 0.2  $\mu\text{m}$ . The thickness L2 of the barrier metal 14 is from about 5 0.005 to 0.05  $\mu\text{m}$ .

As described in the above, in the dual damashine process, since the thin barrier metal 14 formed of  $\text{WN}_x$  or  $\text{WSixNy}$  is interposed between the upper-layer wiring element 16 made of a copper thin film and 10 the interlayer insulating film 8 formed by SOG, and between the via-hole plug 16A made of metal copper and the interlayer insulating film 8 formed by SOG, metal copper of the via-plug 16A and the upper-layer wiring element 16 cannot be diffused into the 15 interlayer insulating film 8. It is therefore possible to prevent the occurrence of segregation and defects. Therefore, the resistance of the via-hole plug 16A and the upper-layer wiring element 16 can be maintained at a low value. In addition, since the adhesiveness does 20 not degrade, it is possible to prevent the metal copper from peeling off.

In the modified example thus constituted, either one of the lower-layer wiring element 4 and the upper-layer wiring element 16 is formed of any one of 25 Al, W, and Cu. The other one of the lower-layer wiring element 4 and the upper-layer wiring element 16 is formed of W or Cu.

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FIG. 2 is a view showing the barrier metal of the present invention applied to a contact hole. In the figure, reference numeral 18 is a source or a drain (conducting layer) of a transistor formed in the substrate 2. Explanation will be made by regarding reference numeral 18 as the source. Reference numeral 20 is an interlayer insulating film which covers the entire transistor including the source 18, thereby insulating it. The insulating film 20 is formed of a SiO<sub>2</sub> film formed by SOG in the same manner explained in FIG. 1. Reference numeral 22 is a contact hole to expose the surface of the source 18 therein. On the inner wall surface of the contact hole and the upper surface of the interlayer insulating film 20, a thin barrier metal 14 made of WN<sub>x</sub> or WSixNy according to the present invention is formed. The contact hole 22 is filled with a contact hole plug 24A made of metal copper, and simultaneously, metal copper is stacked on the upper portion. The metal copper is then subjected to pattern etching to thereby form a wiring element (conducting layer) 24.

Note that, in the figure, the barrier metal 14 on the interlayer insulating film 20 is pattern-etched.

In this case, since the thin barrier metal 14 made  
of  $WN_x$  or  $WSixNy$  is interposed between the interlayer  
insulating film 20 made of  $SiO_2$  and the contact  
hole plug 24A made of metal copper, and between

the interlayer insulating film 20 and the wiring element 24, it is possible to prevent the metal copper from diffusing into the interlayer insulating film 20. Therefore, it is possible to prevent the occurrence 5 of segregation and defects of the metal copper constituting these elements. It is therefore possible not only to maintain a low resistivity but also to prevent the deterioration of adhesiveness, with the result that exfoliation can be prevented.

10 In the aforementioned structure, the drain or source 18 is formed of silicon (Si). The wiring 24 may be formed of Al or W.

FIG. 3 is a view of the barrier metal of the present invention applied to the gate electrode.

15 In the figure, reference numerals 18, 19 are respectively a source and a drain of the transistor device formed in the surface of the substrate 2. A thin gate oxide film 26 is formed between these. A gate electrode 28 is formed on the gate oxide 20 film 26. The gate electrode 28 is formed in a three layered structure by stacking, for example, a phosphorus-doped polysilicon layer 30, a thin barrier metal 14 of  $WN_x$  or  $WSixNy$ , and a metal layer 32 of tungsten, in the order from the bottom.

25 In this case, since the barrier metal 14 of the present invention is interposed between the polysilicon layer 30 and the metal layer 32, it is possible to

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prevent silicon atoms of the polysilicon layer 30 and metallic atoms of the metal layer 32 from diffusing each other. As a result, it is possible to not only prevent the metal layer 32 from being converted into a silicide but also prevent formation of pits (vacant holes) that the resistance of the metal layer 32 can be prevented from increasing and exfoliation of the metal layer 32 can be prevented.

In the aforementioned structure, the metal layer 32 may be formed of Cu. The gate oxide film 26 is formed of any one of  $\text{SiO}_2$ ,  $\text{SiOF}$ ,  $\text{Ta}_2\text{O}_5$  and  $\text{CF}_x$  ( $x = 1-4$ ).

FIG. 4 shows a structure of a capacitor to which the barrier metal of the present invention is applied.

15 A diffusion layer 17 serving as one of the electrodes of the capacitor is formed in the surface of the substrate 2. On the diffusion layer 17, a thin insulating layer 26 is formed as a dielectric layer of the capacitor. On the thin insulating layer 26, 20 a three layered structure of the polysilicon 30/barrier metal 14/metal layer (W) 32 is formed as the other electrode of the capacitor. The barrier metal 14 is formed of  $WN_x$  or  $WSixNy$ . With this structure, the metal layer 32 is not converted into a silicide, 25 so that an increase in resistivity is prevented.

In addition, the exfoliation of the metal layer 32 can be prevented.

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In this case, since the barrier metal 14 of the present invention is interposed between the polysilicon layer 30 and the metal layer 32, it is possible to prevent metal atoms of the metal layer 32 from diffusing into the polysilicon layer 30 by the presence of the barrier metal 14. As a result, it is possible to prevent the metal layer 32 from being converted into a metal silicide layer. It follows that the resistivity of the metal layer 32 is prevented from decreasing and exfoliation of the metal layer 32 is prevented.

In the aforementioned structure, the metal layer 32 may be formed of Cu or Al. The gate oxide film 26 may be formed of any one of  $\text{SiO}_2$ ,  $\text{SiOF}$ ,  $\text{Ta}_2\text{O}_5$ , and  $\text{CF}_x$  ( $X = 1-4$ ).

Next, we will explain a method of forming the aforementioned wiring structure and electrode.

FIG. 5 is a view showing a schematic structure of a processing apparatus for forming the barrier metal. The processing apparatus will be first explained. As shown in the figure, the processing apparatus has a cylindrical shape processing vessel 34 made of aluminium. In the vessel 34, a mounting pedestal 36 is arranged for mounting the substrate 2 thereon. Within the mounting pedestal 36, a heater 38 is provided for heating the substrate 2 to a predetermined process temperature. Note that a heating lamp may be provided

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in a lower portion of the processing vessel to heat the substrate 2 by the lamp.

The processing vessel 34 and the mounting pedestal 36 are individually grounded. The mounting pedestal 36 5 also serves as a lower electrode when a high frequency is used. At the bottom of the processing vessel 34, an exhaust port 40 is provided. To the exhaust port 40, a vacuum exhaust system is connected by way of a vacuum pump 42. To the side wall of the processing 10 vessel 34, a loadlock chamber 44 is connected via a gate valve 41 for transferring the substrate 2 to/from the processing vessel 34.

At the upper portion of the processing vessel 34, a shower head portion 48 having numerous gas spray 15 holes 50 is provided via an insulating material 46. To the shower head portion 48, a high frequency power source 56 of, for example, 13.56 MHz is connected by way of a switch 52 and a matching circuit 54. If a high frequency power is applied, if necessary, 20 to the shower head portion 48 to use it as an upper electrode, plasma processing can be performed. The method for applying a plasma is not limited to this. The high frequency power may be applied to a lower electrode, and alternatively, applied to both 25 upper and lower electrodes.

Furthermore, a plurality of gas sources are connected to the shower head portion 48 via an

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open/shut valve 58 and a mass flow controller 60. As a gas source, a WF<sub>6</sub> source 62, a MMH (monomethylhydrazine) source 64, a SiH<sub>4</sub>(silane) source 66, an NH<sub>3</sub> source 68, a N<sub>2</sub> source 70, an Ar source 72, 5 a H<sub>2</sub> source 74, a ClF<sub>3</sub> source 75 are provided in accordance with different purposes and selectively used. Furthermore, in place of SiH<sub>4</sub> gas, disilane (Si<sub>2</sub>H<sub>4</sub>) or dichlorosilane (SiH<sub>2</sub>Cl<sub>2</sub>) may be used.

10 Then, a method of forming the wiring structure of the present invention using the device constituted as mentioned above will be explained more specifically.

The method of forming the wiring structure of the present invention includes a method of forming the barrier metal at a stretch in one step. Herein below, 15 the method will be explained successively. In this text, a case where dual damashine wiring (refer to FIG. 1) is formed by the aforementioned Cu dual damashine process will be explained as an example. Note that in the case where the barrier metal is applied to a contact hole, the method of forming the barrier metal is completely the same although the steps before/after the step of forming the barrier metal 20 differ.

(1) One-step formation of WSixNy (plasma-less)

25 In the first place, a method of forming a WSixNy barrier metal in one step will be explained. Using another apparatus different from the processing

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apparatus shown in FIG. 5 and in accordance with  
a known method, a SiO<sub>2</sub> interlayer insulating film 8 is  
formed by SOG so as to cover the entire surface of  
the substrate 2 including a SiO<sub>2</sub> insulating layer 6  
5 and a lower-layer wiring 4, as shown in FIG. 6 (A).  
Subsequently, a wiring groove 12 is formed by etching  
in the interlayer insulating film 8 along a wiring  
pattern in accordance with a known method (FIG. 6 (B)).  
Furthermore, a via-hole 10 is formed by etching at a  
10 predetermined portion of the wiring groove 12 to expose  
the lower-layer wiring 4 therein (FIG. 6 (C)).

After processing is applied to the substrate 2,  
the substrate 2 is loaded into a processing apparatus  
shown in FIG. 4 to initiate the formation of the  
15 barrier metal.

After the substrate 2 is placed on the mounting  
pedestal 36 of the processing vessel 34, the processing  
vessel 34 is sealed airtight. The substrate 2 is  
maintained under a predetermined processing pressure  
20 and simultaneously a predetermined processing gas is  
introduced from the shower head portion 48 while the  
processing vessel 34 is vacuum-evacuated and maintained  
at a predetermined processing pressure. Under these  
conditions, a process for forming the barrier metal is  
25 carried out. By supplying WF<sub>6</sub> gas, SiH<sub>4</sub> gas, and MMH  
gas separately as processing gases and employing  
plasma-less thermal CVD (Chemical Vapor Deposition),

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the barrier metal 14 of the  $WSixNy$  film is formed at a stretch to a predetermined thickness in one step (FIG. 6(D)).

As the substrate 2, an 8-inch wafer is used  
5 herein. The processing gases,  $WF_6$  gas,  $SiH_4$  gas, and MMH gas are supplied at flow rates of about 2-20 sccm, 10-300 sccm, and 1-10 sccm, respectively. The processing temperature is about 300-450°C. The processing pressure is about 0.4-80 Torr. In the case  
10 where dichlorosilane is used in place of silane, the other gases are supplied at the same flow rates and the same processing pressure is employed but the processing temperature is about 550-650°C. Note that these numerical values mentioned about as well as the  
15 numerical values which will be described later are only examples, so that these numerical values may be appropriately changed in order to obtain the most suitable conditions.

If this method is employed, it is possible to form  
20 the barrier metal 14 in one step. As a result, the number of the steps can be reduced.

When the formation of the barrier metal 14 is completed in this method, for example, the substrate 2 is unloaded from the processing apparatus.  
25 Subsequently, metal copper is deposited on the surface of the substrate 2 as a wiring metal and by CVD (chemical Vapour Deposition) simultaneously fill the

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via-hole 10 and the wiring groove 12. In this manner, the via-hole 10 is filled with the via-hole plug 16A and the upper-layer wiring 16 is formed in the wiring groove 12 (FIG. 6 (E)).

5 Note that the CVD processing of the metal copper may be carried out in the same processing apparatus as used in forming the barrier metal.

10 Subsequently, the substrate having the metal copper deposited thereon is taken out from the processing apparatus and subjected to CMP (Chemical Mechanical Polishing) to polish and remove unnecessary metal copper of the upper surface. The wiring pattern of the upper layer is thus formed (FIG. 6 (F)).  
15 In this manner, the Cu dual damashine wiring is completed.

In this embodiment, MMH gas is used as a gas for use in mixing nitrogen atoms into the barrier metal 14. However, in place of this, NH<sub>3</sub> gas or N<sub>2</sub> gas may be used. If necessary, an inert gas such as Ar gas  
20 may be used as a carrier gas. In place of SiH<sub>4</sub> gas, dichlorosilane, disilane or the like may be used.

(2) One-step formation of WN<sub>X</sub> (plasma-less)

Then, we will explain a method of forming WN<sub>X</sub> barrier metal in one step. The same manner is employed in the steps except the step shown in FIG. 6 (D), so that we will explain only the manner employed in the step shown in FIG. 6 (D). In this case, the barrier

metal 14 consisting of the  $WN_x$  film is formed at a stretch to a predetermined thickness in one step by supplying  $WF_6$  gas and MMH gas as processing gases and in accordance with the plasma-less thermal CVD method.

In the case of an 8-inch wafer, the processing gas, WF<sub>6</sub> gas is supplied at a flow rate of about 5-80 sccm and MMH gas at a flow rate of about 1-20 sccm. The processing temperature is about 300-450°C and the processing pressure is about 0.5 to 80 Torr.

In this case, since only two types of processing gases are used, the structure of a gas supply system can be drastically simplified. Also in this case, needless to say, NH<sub>3</sub> gas or N<sub>2</sub> gas may be used in place of MMH gas.

(3) Two-step formation of  $\text{WSi}_x\text{N}_y$

Then, we will explain a method of forming a WSixNy barrier metal in two steps. In this case, after the step shown in FIG. 6 (C) is completed, the WSi layer is formed in the processing apparatus shown in FIG. 5. WF<sub>6</sub> gas and SiH<sub>4</sub> gas are used as the processing gases. The processing gases are supplied with or without using the carrier gas such as Ar gas to deposit the WSi film by plasma-less thermal CVD. The processing gas, WF<sub>6</sub> gas is supplied at a flow rate of about 2-80 sccm and SiH<sub>4</sub> gas is at about 5-40 sccm in the case of an 8-inch wafer. The processing temperature is about 300 to

450°C. The processing pressure is about 0.5 to 80 Torr. Needless to say, dichlorsilane, disilane, or the like may be used in place of SiH<sub>4</sub>.

When the formation of the WSi film is thus completed, supply of WF<sub>6</sub> gas and SiH<sub>4</sub> gas is shut off and then, MMH gas is supplied to nitride the WSi film, with the result that the WSixNy barrier metal 14 is formed. At this time, the flow rate of the MMH gas is about 1 to 20 sccm. The processing temperature is about 300 to 450°C. The processing pressure is about 0.5 to 10 Torr. In this manner, the formation of the barrier metal 14 is completed. The nitridation is performed by using MMH gas herein because the processing can be made at a low temperature, so that a side reaction product is relatively rarely generated. It is therefore favorable to solve a problem with particles.

In this case, NH<sub>3</sub> gas or N<sub>2</sub> gas may be used in place of the MMH gas. Furthermore, it is preferable that the WF<sub>6</sub> gas be completely removed by purging N<sub>2</sub> gas into the processing vessel 34, between the film formation step and the nitriding step. In particular, when the NH<sub>3</sub> gas is used in place of the MMH gas in the nitriding step, if the WF<sub>6</sub> gas remains in the processing vessel, a side product, which is difficult to remove, is formed by the reaction between ammonia and fluoride gas. It is therefore preferred to

completely remove the WF<sub>6</sub> gas before the nitriding process. When the NH<sub>3</sub> gas is used, the processing temperature is about 300 to 450°C.

In the case where N<sub>2</sub> gas is used in place of MMH  
5 gas, the switch 52 is turned on to apply a high frequency power between an upper electrode (shower head portion) 48 and a lower electrode (mounting table) 36. In this manner, a plasma is generated in the interior of the vessel to perform the nitriding process for the  
10 surface of WSi film. At this time, the supply amount of N<sub>2</sub> gas is about 50-300 sccm, the processing temperature is about 300 to 450°C, and the processing pressure is about 0.1 to 5 Torr (each of the conditions is for 8 inch wafer).

15 As described in the above, if two steps are carried out in the same processing apparatus, it is possible to cut down the time required for transferring of the water. As a result, the throughput can be improved. Needless to say, the film formation step and  
20 the nitriding step may be performed in discrete processing apparatuses.

(4) Two-step formation of WN<sub>X</sub>

Then, we will explain a method of forming a WN<sub>X</sub> barrier metal in two steps. In this case, after  
25 the step shown in FIG. 6(C) is completed, a W layer is first formed in the apparatus shown in FIG. 5. At this time, WF<sub>6</sub> gas and H<sub>2</sub> gas are used as the

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processing gases to deposit the W film by the plasma-less thermal CVD. The flow rates of the processing gases, WF<sub>6</sub> gas and H<sub>2</sub> gas are about 5-100 sccm and about 100-1000 sccm. The processing temperature is  
5 about 300-450°C, the processing pressure is about 1 to 80 Torr.

When the formation of the W film is completed in this way, the supply of the WF<sub>6</sub> gas and the H<sub>2</sub> gas is shut off, and subsequently, MMH gas is supplied and  
10 thereby nitrides the W film to form the WN<sub>X</sub> barrier metal 14.

The flow rate of the MMH gas at this time is about 1-10 sccm; the processing temperature is about 300-450°C, and the processing pressure is about 0.1 to  
15 5 Torr, in the case of an 8-inch wafer. In this manner, the formation of the barrier metal 14 is completed. The nitriding is performed by using MMH gas herein because the processing can be made at a low temperature, so that a side reaction product is  
20 relatively rarely generated. It is therefore favorable to solve a problem with particles.

In this case, NH<sub>3</sub> gas or N<sub>2</sub> gas may be used in place of MMH gas as explained in the above (3). Furthermore, it is preferable that the WF<sub>6</sub> gas be  
25 completely removed by purging N<sub>2</sub> gas into the processing vessel 34, between the film formation step and the nitriding step. In particular, when NH<sub>3</sub> gas is

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used in place of MMH gas in the nitriding step, if the WF<sub>6</sub> gas remains in the processing vessel, a side product, which is difficult to remove, is formed by the reaction between ammonia and fluoride gas. It is therefore preferred to completely remove the WF<sub>6</sub> gas before the nitriding process. When NH<sub>3</sub> gas is used, the processing temperature is about 300-450°C.

When N<sub>2</sub> gas is used in place of MMH gas, the switch 52 is turned on to apply a high frequency power between the upper electrode (shower head portion) 48 and the lower electrode (mounting table) 36. In this manner, a plasma is generated in the interior of the vessel to perform nitriding process for the surface of WSi film. At this time, the supply amount of N<sub>2</sub> gas is about 50-300 sccm, the processing temperature is about 300 to 450°C, and the processing pressure is about 0.1 to 5 Torr.

As described in the above, if two steps are carried out in the same processing apparatus, it is possible to cut down the time required for transferring of the water. As a result, the throughput is improved. Needless to say, the film formation step and the nitriding step may be performed in discrete processing apparatuses.

The barrier metal 14 formed by each of the aforementioned methods was checked for characteristics. As a result, it was confirmed that the barrier metal

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has sufficiently high barrier properties to oxygen atoms or silicon atoms.

Next, the gate electrode of the present invention and the method of forming the gate electrode will be explained.

Now, the gate electrode 28, which has been explained with reference to FIG. 3, will be explained more specifically. FIG. 7 is a magnified view of a part of the gate electrode shown in FIG. 3.

10 We will explain the case in which tungsten nitride  
(WN<sub>x</sub>) is used as the barrier metal 14 as an example.  
As explained in FIG. 3, a source 18 and a drain 19  
are formed at both sides of the gate oxide film 26  
over the substrate 2 such as a single crystalline  
15 silicon semiconductor wafer, as explained in FIG. 3.  
As the gate oxide film 26, a silicon oxide film (SiO<sub>2</sub>)  
is used.

For example, a phosphorus-doped polysilicon layer 30 is formed in the different film formation apparatus as mentioned above and in accordance with a known method, and thereafter, the substrate W is loaded into the film formation apparatus as shown in FIG. 5.

The WN<sub>x</sub> film may be formed either by a single step using the aforementioned plasma-less CVD or by two-steps.

When the WN<sub>x</sub> film is formed in the single step, WF<sub>6</sub> gas and MMH gas are supplied as the processing

gases to form the barrier metal of the  $WN_x$  film on the polysilicon layer 30 at a predetermined thickness in accordance with the plasma-less thermal CVD. The processing gas,  $WF_6$  gas is supplied at a flow rate of about 5-80 sccm and MMH gas at a flow rate of about 1-20 sccm, in the case of an 8-inch wafer. The processing temperature is about 300-450°C and the processing pressure is about 0.5 to 80 Torr.

In this case, since the number of gas types is only two, the structure of the gas supply system can be drastically simplified.  $NH_3$  gas or  $N_2$  gas may be used in place of MMH gas.

In the case where the  $WN_x$  film is formed in two steps, the W layer is first formed. At this time,  $WF_6$  gas and  $H_2$  gas are used as the processing gases to deposit the W film by the plasma-less thermal CVD. As the processing gas,  $WF_6$  gas is supplied at a flow rate of about 5-100 sccm and  $H_2$  gas at a flow rate of about 100-1000 sccm in the case of an 8-inch wafer. The processing temperature is about 300-450°C and the processing pressure is about 1 to 80 Torr.

When the formation of the W film is thus completed, supply of  $WF_6$  gas and  $H_2$  gas is shut off. Subsequently, MMH gas is supplied to nitride the W film, to obtain the barrier metal 14 of  $WN_x$ . At this time, the flow rate of the MMH gas is about 1 to 10 sccm, the processing temperature is about 300

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to 450°C, and the processing pressure is about 0.1 to 5 Torr. In this manner, the formation of the barrier metal 14 is completed. The nitriding is performed by using MMH gas herein because the processing can be made at a low temperature, so that a side reaction product is relatively rarely generated. It is therefore favorable to solve a problem with particles.

In this case, NH<sub>3</sub> gas or N<sub>2</sub> gas may be used in place of the MMH gas. Furthermore, it is preferable that the WF<sub>6</sub> gas be completely removed by purging N<sub>2</sub> gas into the processing vessel 34, between the film formation step and the nitriding step. In particular, when the NH<sub>3</sub> gas is used in place of the MMH gas in the nitriding step, if the WF<sub>6</sub> gas remains in the processing vessel, a side product, which is difficult to remove, is formed by the reaction between ammonia and fluoride gas. It is therefore preferred to completely remove the WF<sub>6</sub> gas before the nitriding process. When the NH<sub>3</sub> gas is used, the processing temperature is about 300 to 450°C.

After the WN<sub>x</sub> barrier metal 14 is thus formed in the single step or the two steps, an upper tungsten layer 32 is formed in the same processing vessel 34. The film formation conditions for the tungsten layer 32 are the same as in the film formation step of the W film performed before the WN<sub>x</sub> layer is formed in the two-step process previously mentioned. Using WF<sub>6</sub>

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gas and H<sub>2</sub> gas as the processing gases, the W film is deposited to a predetermined thickness in accordance with the plasma-less thermal CVD. At this time, a flow rate of the processing gas, WF<sub>6</sub> gas, is about 5-100 sccm and the H<sub>2</sub> gas about 100-1000 sccm. The processing temperature is about 300 to 450°C. The processing pressure is about 1 to 80 Torr. At this time, each of the layers is set such that a design rule for the memory corresponding to, for example, 1G bit capacity is used. More specifically, the gate oxide film 26 is about 20Å thick, the polysilicon layer 30 is about 500Å thick, the barrier metal 14 is 50Å thick and the metal layer (tungsten) layer 32 is 500Å thick.

15 The tungsten layer 32 is formed in this manner to thereby form the gate electrode 28. The barrier metal 14 and the tungsten layer 32 are made of the same metallic material, namely, tungsten, so that they are continuously formed in the same film formation apparatus. Therefore, the loading/unloading operation 20 of the substrate is not required, with the result that the yield can be improved.

Since the WN<sub>x</sub> layer is used as the barrier metal in the polysilicon metal gate electrode, it is possible to obtain resistance at an extremely low value. In addition, adhesiveness and heat resistance between both layers can be maintained high and high barrier properties are exhibited. In particular, even

if the barrier metal 14 is reduced in thickness up to about 50Å, the sufficient barrier properties as mentioned above can be obtained. It is therefore possible to attain a thin-film and multi-layered 5 semiconductor integrated circuit.

The gate electrode of the present invention and a conventional gate electrode generally used were checked for characteristics. The results are shown in FIG. 9.

10 In FIG. 9, Comparative Examples 1 and 2 show a conventional gate electrode. More specifically, Comparative Example 1 is the gate electrode formed of the polysilicon layer and the tungsten silicide layer. Comparative Example 2 is the gate electrode formed of 15 the polysilicon layer and titanium silicide layer.

As is apparent from FIG. 9, the gate electrode of the present invention is excellent in both resistance value and heat resistance which are critical characteristics as the gate electrode. Furthermore, it 20 is demonstrated that the gate electrode of the present invention is satisfactory in chemical resistance, that is, corrosiveness to hydrogen fluoride (HF), and in etching properties during the film formation. Note that the low etching property during the film formation 25 means that the film thickness is controlled well. Therefore, it is possible to form a thin-film gate electrode can be formed with a high accuracy.

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In contrast, in Comparative Example 1, heat resistance is good but a critical factor, resistance value, is considerably large. For this reason, Comparative Example 1 is not preferable.

- 5 In Comparative Example 2, the resistance value is large and heat resistance is lower than the reference value of 850°C. For this reason, Comparative Example 2 is not preferable.

In the aforementioned embodiments, the case where 10  $\text{SiO}_2$  is used as the gate oxide film 26 is explained as an example. However, the present invention is not limited to this. Tantalum oxide ( $\text{Ta}_2\text{O}_5$ ) enabling a further reduction of the film thickness may be used as the gate oxide film 26.

- 15 FIG. 8 is a magnified sectional view of the gate electrode when  $\text{Ta}_2\text{O}_5$  is used as the gate oxide film. In the case of the gate electrode shown in FIG. 8, a  $\text{WN}_x$  barrier metal 14 is directly formed on the  $\text{Ta}_2\text{O}_5$  gate oxide film 26 in place of using the polysilicon 20 layer. On the barrier metal 14, the tungsten layer 32 is further formed.

The barrier metal 14 and the tungsten layer 32 are formed continuously in the same film formation apparatus, as shown in the above. Also, in this case, 25 the  $\text{WN}_x$  barrier metal 14 not only exhibits efficient barrier properties but also contributes to further reducing the thickness of the gate electrode 28 since

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the polysilicon layer is not used. The total thickness of the gate oxide film 26, barrier metal 14 and the tungsten layer 32 can be reduced up to, for example, about 1000Å. As a result, a design rule of the memory of 4G bit capacity can be applied thereto.

Now,  $WN_x$  and  $WSixNy$  used in the embodiments of the present invention can be cleaned with a gas including  $ClF_3$  gas in the same manner as in other major films. If cleaning is performed every time a film is formed on the appropriate number of wafers, it is possible to suppress generation of particles to obtain a high-quality film.

In the aforementioned embodiments, the case where tungsten is used as a high-melting point metallic material, is explained as an example. The present invention is not limited to this. For example, molybdenum (Mo) may be used. Furthermore, in the aforementioned embodiments, the case where a semiconductor wafer is used as the substrate is explained as an example. However, the present invention is not limited to this. Needless to say, an LCD substrate and a glass substrate may be used.

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*Assigned to filed 8-19-99*

526 Rec'd PCT/PTO 05 MAY 2000

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CLAIMS

1. (deleted)
2. (deleted)
3. (deleted)

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**ART 34 AMDT**

4. (deleted)
5. (deleted)
6. (deleted)
9. An electrode of a circuit element formed on a  
5 semiconductor substrate, comprising:
  - a polysilicon layer;
  - a barrier metal formed on the polysilicon layer;and
  - a metal layer formed on the barrier metal,  
10 wherein the barrier metal is formed of  $WSixNy$   
(tungsten silicide nitride).

ART 34 AMDT

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10. The electrode according to claim 9, wherein  
the electrode is a gate electrode of a transistor; the  
polysilicon layer is formed on a gate insulating film  
formed between a source and a drain of the transistor.

5 11. The electrode according to claim 9 or 10,  
wherein the metal layer is formed of W or Cu.

12. The electrode according to claim 11, wherein  
the gate insulating film is formed of any one of SiO<sub>2</sub>,  
SiOF, Ta<sub>2</sub>O<sub>5</sub>, and CF<sub>x</sub>.

10 13. A gate electrode of a transistor formed on a  
semiconductor substrate, comprising:

a gate insulating film formed between a source and  
a drain of the transistor;

15 a barrier metal formed on the gate insulating  
film; and

a metal layer formed on the barrier metal,  
wherein the barrier metal is formed of WSixNy  
(tungsten silicide nitride).

20 14. The electrode according to claim 9, wherein  
the electrode is a capacitor electrode and the  
polysilicon layer is formed on an insulating film.

15. The electrode according to claim 14, wherein  
the metal layer is formed of any one of Al, W, and Cu.

25 16. The electrode according to claim 15, wherein  
the insulating film is formed of formed of any one of  
SiO<sub>2</sub>, SiOF, Ta<sub>2</sub>O<sub>5</sub>, and CF<sub>x</sub>.

17. (deleted)

ART 34 AMDT

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18. (deleted)

19. (deleted)

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ART 34 AMDT

20. (deleted)
23. (deleted)
24. A method of forming a gate electrode of  
a transistor formed on a semiconductor substrate,  
comprising  
forming a barrier metal of  $WSixNy$  (tungsten  
silicide nitride) on a gate insulating film formed  
between a source and a drain of a transistor; and  
forming a conducting layer on the barrier metal.

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25. A method of forming a gate electrode of  
a transistor formed on a semiconductor substrate;  
comprising  
    forming a polysilicon layer on a gate insulating  
5     film formed between a source and a drain of a  
transistor;  
    forming a barrier metal of  $WSi_xN_y$  (tungsten  
silicide nitride) on the polysilicon layer; and  
    forming a conducting layer on the barrier metal.  
10     26. The method according to claim 24 or 25,  
wherein the conducting layer is formed of W or Cu.  
    27. The method according to claim 24 or 25,  
wherein the gate insulating film is formed any one of  
 $SiO_2$ ,  $SiOF$ ,  $Ta_2O_5$ , and  $CF_x$ .

## A B S T R A C T

A wiring structure of a semiconductor device according to the present invention comprises a first conducting layer for electrically connecting with a semiconductor element or a wiring element formed on a semiconductor substrate, a barrier metal formed on the first conducting layer, and a second conducting layer formed on the barrier metal, for electrically connecting with the first conducting layer via the barrier metal, in which the barrier metal is formed of  $WN_x$  (tungsten nitride) or  $WSi_xN_y$  (tungsten silicide nitride).

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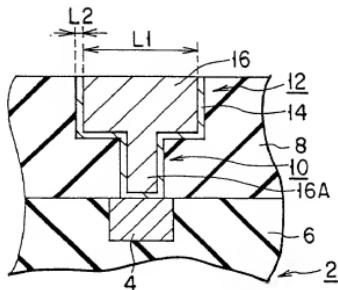


FIG. 1

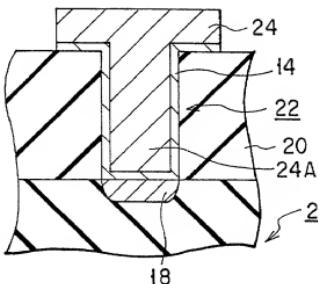


FIG. 2

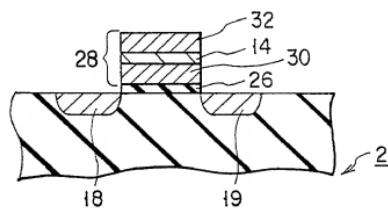


FIG. 3

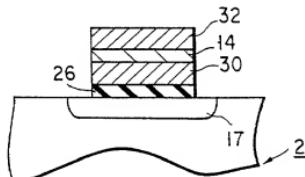


FIG. 4

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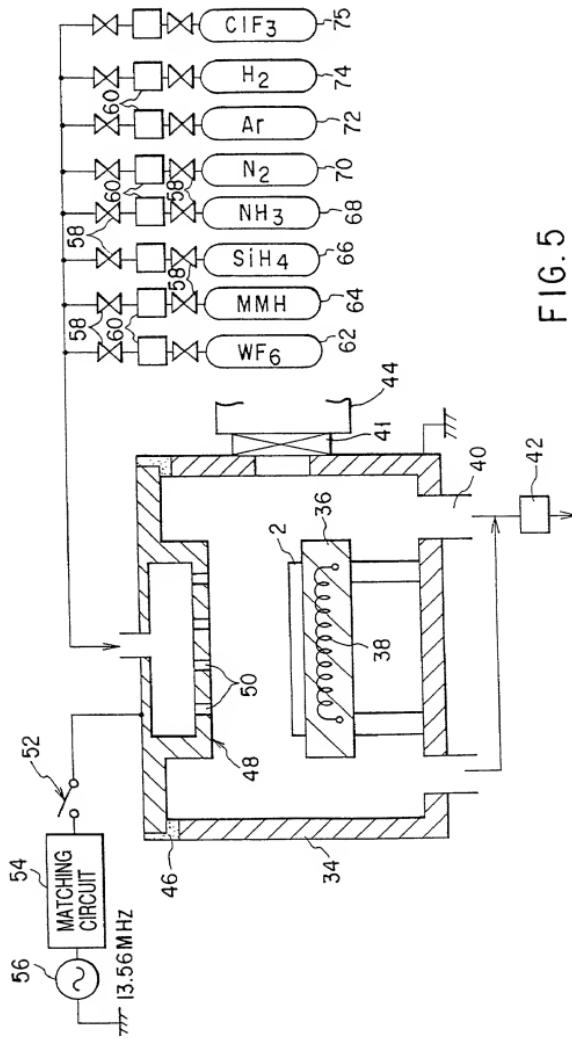


FIG. 5

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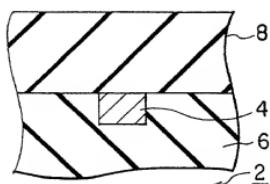


FIG. 6A

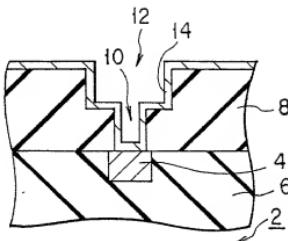


FIG. 6D

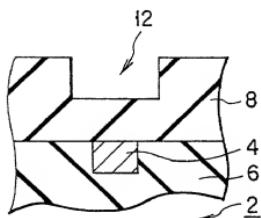


FIG. 6B

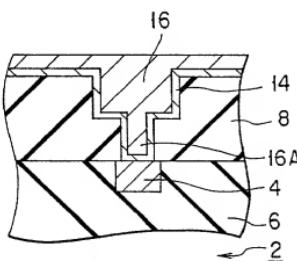


FIG. 6E

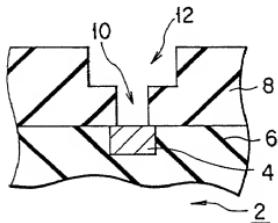


FIG. 6C

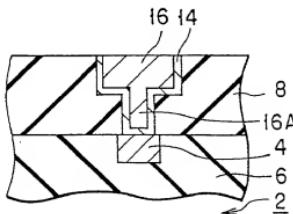


FIG. 6F

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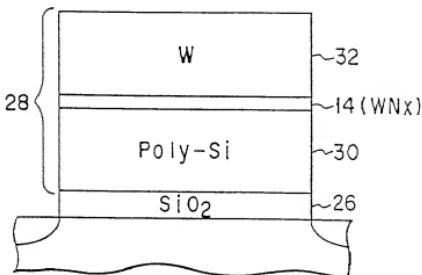


FIG. 7

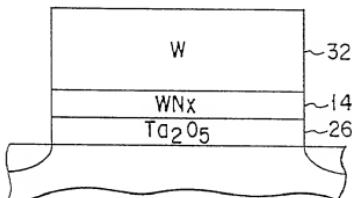


FIG. 8

	COMPARATIVE EXAMPLE 1	COMPARATIVE EXAMPLE 2	PRESENT INVENTION
STRUCTURE	Poly / WSi	Poly / TiSi	Poly / WN / W
RESISTANCE VALUE (uohmcm)	50 - 60	20 - 30	10
HEAT RESISTANCE (°C)	1000	800	900
CHEMICAL RESISTANCE (HF)	GOOD	POOR	GOOD
ETCHING AMOUNT DURING FILM FORMATION	LARGE	SMALL	SMALL

FIG. 9

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## Declaration Power of Attorney For Patent Application

特許出願宣言書及び委任状  
Japanese Language Declaration

## 日本語宣言書

下記の氏名の発明者として、私は以下の通り宣言します。

As a below named inventor, I hereby declare that:

私の住所、私書箱、国籍は下記の私の氏名の横に記載された通りです。

My residence, post office address and citizenship are as stated below next to my name.

下記の名称の発明に関して請求範囲に記載され、特許出願している発明内容について、私が最初かつ唯一の発明者（下記の氏名が一つの場合）もしくは最初かつ共同発明者であると（下記の名称が複数の場合）信じています。

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

半導体デバイスの配線構造、電極、及びこれらを形成する方法

WIRING STRUCTURE AND ELECTRODE OF SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

上記発明の明細書（下記の欄で×印がついていない場合は、本書に添付）は、

The specification of which is attached hereto unless the following box is checked:

1998. 11月5日に提出され  
米国出願番号または特許協定条約  
国際出願番号を PCT/JP98/04983 とし、  
(該当する場合) 1999. 4月8日 及び  
1999. 8月19日に訂正されました。

was filed on November 5, 1998,  
as United States application Number or  
PCT international Application Number  
PCT/JP98/04983 and was amended on  
April 8, 1999 and August 19, 1999 (if applicable).

私は、特許請求範囲を含む上記訂正後の明細書を検討し、内容を理解していることをここに表明します。

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

私は、連邦規則法典第37編第1条56項に定義されるとおり、特許資格の有無について重要な情報を開示する義務があることを認めます。

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56

## Japanese Language Declaration

(日本語宣言書)

私は、合衆国法典第35編第119条(a)~(d)項又は第365条(b)に基づき下記の、米国以外の國の少なくとも一ヶ国を指定している特許協力条約365(a)項に基づく国際出願、又は外国での特許出願もしくは発明者証の出願についての外国優先権をここに主張するとともに、優先権を主張している、本出願の前に出願された特許または発明者証の外国出願を以下に、枠内をマークすることで、示しています。

I hereby claim foreign priority under Title 35, United States Code, Section 119(a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 365(a) of any PCT international application which designated at least one country other than the United States, listed below and have also identified below by checking the box any foreign application for patent or inventor's certificate, or PCT international application having a filing date before that of the application on which priority is claimed:

## Prior Foreign Application(s)

外国での先行出願

Prior Foreign Application(s) (番号)	JAPAN (Country) (国名)	Priority Not Claimed 優先権の主張なし
9-319059		<input type="checkbox"/>
10-207198	JAPAN	<input type="checkbox"/>
		<input type="checkbox"/>
		<input type="checkbox"/>
		<input type="checkbox"/>

私は、第35条米国法典第119条(e)項に基いて下記の米国特許出願規定に記載された権利をここに主張いたします。

I hereby claim the benefit under Title 35, United States Code, Section 119(e) of any United States provisional application(s) listed below.

(Application No.) (出願番号)	(Filing Date) (出願日)	(Application No.) (出願番号)	(Filing Date) (出願日)

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## Japanese Language Declaration

(日本語宣言書)

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## Japanese Language Declaration

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